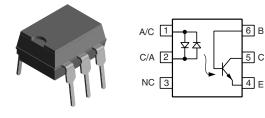
## **Vishay Semiconductors**

# Optocoupler, Phototransistor Output, AC Input, with Base Connection



i179010

## DESCRIPTION

The H11AA1 is a bi-directional input optically coupled isolator consisting of two inverse parallel gallium arsenide infrared LEDs coupled to a silicon NPN phototransistor in a 6 pin DIP package. The H11AA1 has a minimum CTR of 20 %, a CTR symmetry of 1:3 and is designed for applications requiring detection or monitoring of AC signals.

## **FEATURES**

- AC or polarity insensitive input
- · Built-in reverse polarity input protection
- I/O compatible with integrated circuits
- Industry standard DIP package
- Isolation test voltage: 5300 V<sub>RMS</sub>
- · Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

### APPLICATIONS

- Telephone line detection
- AC line motor
- PLC
- Instrumentation

### AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- CSA 93751
- BSI IEC 60950; IEC 60065
- DIN EN 60747-5-5 available with option 1
- FIMKO

ORDER INFORMATION				
PART	REMARKS			
H11AA1	CTR > 20 %, DIP-6			
H11AA1-X006	CTR > 20 %, DIP-6 400 mil (option 6)			
H11AA1-X007	CTR > 20 %, SMD-6 (option 7)			
H11AA1-X009	CTR > 20 %, SMD-6 (option 9)			

#### Note

For additional information on the available options refer to option information.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
INPUT				•		
Forward continuous current		I <sub>F</sub>	60	mA		
Power dissipation		P <sub>diss</sub>	100	mW		
Derate linearly from 25 °C			1.3	mW/°C		
OUTPUT						
Power dissipation		P <sub>diss</sub>	200	mW		
Derate linearly from 25 °C			2.6	mW/°C		
Collector emitter breakdown voltage		BV <sub>CEO</sub>	30	V		
Emitter base breakdown voltage		BV <sub>EBO</sub>	5	V		
Collector base breakdown voltage		BV <sub>CBO</sub>	70	V		



# Vishay Semiconductors

## Optocoupler, Phototransistor Output, AC Input, with Base Connection



ABSOLUTE MAXIMUM RATINGS							
PARAMETER	TEST CONDITION	SYMBOL VALUE		UNIT			
COUPLER							
Isolation test voltage (RMS)	between emitter and detector, referred to standard climate 23 °C/50% RH, DIN 50014	V <sub>ISO</sub>					
Creepage distance			≥7	mm			
Clearance distance			≥ 7	mm			
Comparative tracking index	per DIN IEC 112/VDE 0303, part 1	CTI	175				
Isolation resistance	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 25 ^{\circ}\text{C}$	R <sub>IO</sub>	≥ 10 <sup>12</sup>	Ω			
	$V_{IO} = 500 \text{ V}, \text{ T}_{amb} = 100 ^{\circ}\text{C}$	R <sub>IO</sub>	≥ 10 <sup>11</sup>	Ω			
Storage temperature range		T <sub>stg</sub>	- 55 to + 150	°C			
Operating temperature range		T <sub>amb</sub>	- 55 to + 100	°C			
Lead soldering time at 260 °C		T <sub>sld</sub>	10	S			

#### Note

 $T_{amb} = 25$  °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

ELECTRICAL CHARACTERISTCS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	I <sub>F</sub> = 10 mA	VF		1.2	1.5	V
OUTPUT						
Collector emitter breakdown voltage	$I_{\rm C} = 1  \rm{mA}$	BV <sub>CEO</sub>	30			V
Emitter base breakdown voltage	I <sub>E</sub> = 100 μA	BV <sub>EBO</sub>	5			V
Collector base breakdown voltage	I <sub>C</sub> = 100 μA	BV <sub>CBO</sub>	70			V
Collector emitter leakage current	V <sub>CE</sub> = 10 V	I <sub>CEO</sub>		5	100	nA
COUPLER						
Collector emitter saturation voltage	I <sub>F</sub> = 10 mA, I <sub>C</sub> = 0.5 mA	V <sub>CEsat</sub>			0.4	V

#### Note

 $T_{amb} = 25 \ ^{\circ}C$ , unless otherwise specified.

Minimum and maximum values were tested requierements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
DC current transfer ratio	I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V	CTR <sub>DC</sub>	20			%
Symmetry (CTR at + 10 mA)/(CTR at - 10 mA)			0.33	1	3	



Optocoupler, Phototransistor Output, AC Input, with Base Connection **Vishay Semiconductors** 

H11AA1

### **TYPICAL CHARACTERISTICS**

T<sub>amb</sub> = 25 °C, unless otherwise specified

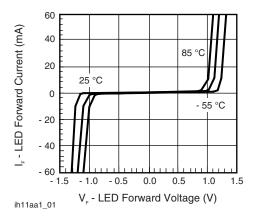


Fig. 1 - LED Forward Current vs.Forward Voltage

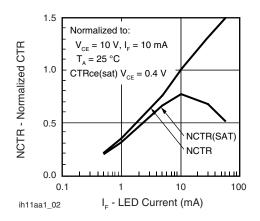


Fig. 2 - Normalized Non-Saturated and Saturated CTR vs. LED Current

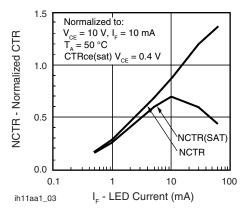


Fig. 3 - Normalized Non-Saturated and Saturated CTR vs. LED Current

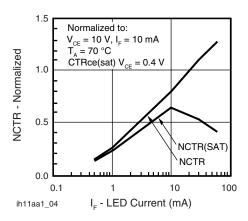


Fig. 4 - Normalized Non-Saturated and Saturated CTR vs. LED Current

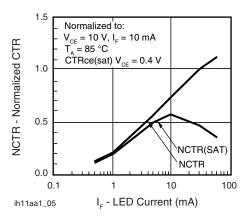


Fig. 5 - Normalized Non-Saturated and Saturated CTR vs. LED Current

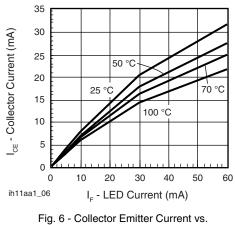


Fig. 6 - Collector Emitter Current vs. Temperature and LED Current

# H11AA1

## **Vishay Semiconductors**

Optocoupler, Phototransistor Output, AC Input, with Base Connection



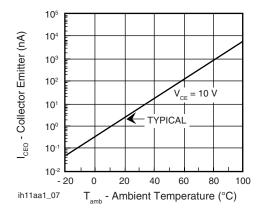


Fig. 7 - Collector Emitter Leakage Current vs. Temperature

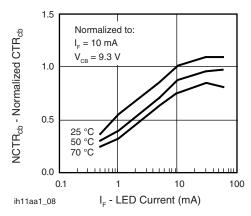


Fig. 8 - Normalized CTR<sub>cb</sub> vs. LED Current and Temperature

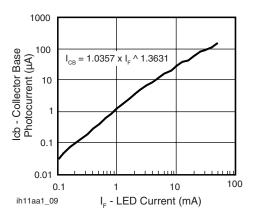


Fig. 9 - Collector Base Photocurrent vs. LED Current

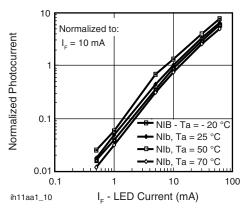


Fig. 10 - Normalized Photocurrent vs. LED Current

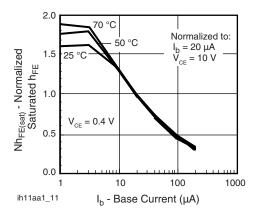
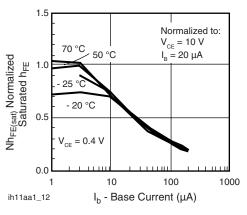
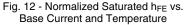


Fig. 11 - Normalized Saturated h<sub>FE</sub> vs. Base Current and Temperature







Optocoupler, Phototransistor Output, AC Input, with Base Connection Vishay Semiconductors

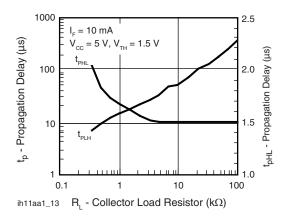
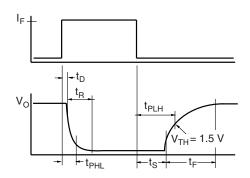
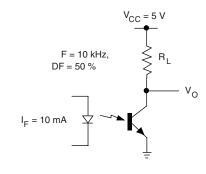


Fig. 13 - Propagation Delay vs. Collector Load Resistor

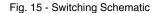


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Fig. 14 - Switching Waveform



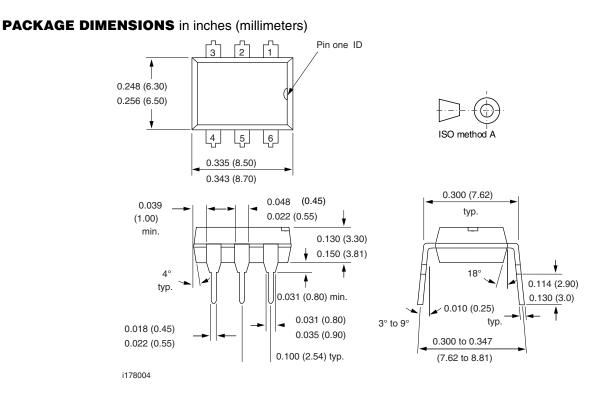
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## Vishay Semiconductors Optocour

Optocoupler, Phototransistor Output, AC Input, with Base Connection

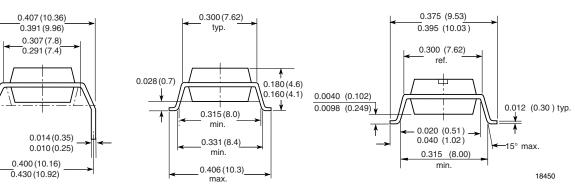




**Option 6** 



**Option 9** 





Optocoupler, Phototransistor Output, AC Input, with Base Connection

## Vishay Semiconductors

### **OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



Vishay

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